

Evaluation of Mg compounds as coating materials in Mg batteries

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S1. Mg-binary and ternary compounds

Table S1: List of the specific Mg-binaries whose reductive and oxidative stabilities have been evaluated.

Mg-X	Binaries
Mg-B	MgB ₂
	MgB ₄
	MgB ₇
Mg-Si	Mg ₂ Si
	Mg ₉ Si ₅
	Mg ₅ Si ₆
Mg-C	Mg ₂ C ₃
	MgC ₂
Mg-As	Mg ₃ As ₂
Mg-P	Mg ₃ P ₂
	MgP ₄
Mg-N	Mg ₃ N ₂
Mg-Te	MgTe
Mg-Se	MgSe
Mg-S	MgS
Mg-O	MgO
Mg-I	MgI ₂
Mg-Br	MgBr ₂
Mg-Cl	MgCl ₂
Mg-F	MgF ₂
Mg-H	MgH ₂

Table S2: List of the specific Mg-ternaries whose reductive and oxidative stabilities have been evaluated.

Mg-X-Y	Ternaries
Mg-In-Te	$\text{Mg}(\text{InTe}_2)_2$
Mg-Si-Se	Mg_2SiSe_4
Mg-P-Se	MgPSe_3
Mg-Sc-Se	$\text{Mg}(\text{ScSe}_2)_2$
Mg-In-Se	$\text{Mg}(\text{InSe}_2)_2$
Mg-Ge-Se	Mg_2GeSe_4
Mg-Si-S	Mg_2SiS_4
Mg-Ge-S	Mg_2GeS_4
Mg-P-S	MgPS_3
Mg-Al-S	$\text{Mg}(\text{AlS}_2)_2$
Mg-Ga-S	$\text{Mg}(\text{GaS}_2)_2$
Mg-Sc-S	$\text{Mg}(\text{ScS}_2)_2$
Mg-In-S	$\text{Mg}(\text{InS}_2)_2$
Mg-B-H	$\text{Mg}(\text{BH}_4)_2$
Ternary oxides	
Mg-B-O	$\text{Mg}_3(\text{BO}_3)_2$
	$\text{Mg}_2\text{B}_2\text{O}_5$
	$\text{MgO}(\text{B}_2\text{O}_3)_2$
Mg-Si-O	$\text{Mg}_{14}\text{Si}_5\text{O}_{24}$
	Mg_2SiO_4
	MgSiO_3
Mg-C-O	MgCO_3
Mg-As-O	$\text{Mg}_2\text{As}_2\text{O}_7$
Mg-P-O	$\text{Mg}_3(\text{PO}_4)_2$
	$\text{Mg}_2\text{P}_2\text{O}_7$
	$\text{Mg}(\text{PO}_3)_2$
	$\text{MgP}_4\text{O}_{11}$
Mg-N-O	$\text{Mg}(\text{NO}_3)_2$
Mg-Te-O	Mg_3TeO_6
	$\text{Mg}_2\text{Te}_3\text{O}_8$
	$\text{MgTe}_6\text{O}_{13}$
Mg-Se-O	MgSeO_3
	MgSeO_4
	MgSe_2O_5
Mg-S-O	MgSO_4
	MgS_2O_7
Mg-I-O	$\text{Mg}(\text{IO}_3)_2$
Mg-Cl-O	$\text{Mg}(\text{ClO}_4)_2$
Mg-Ti-O	Mg_2TiO_4
	MgTiO_3
	$\text{Mg}_3\text{Ti}_9\text{O}_{20}$
	$\text{Mg}_{11}\text{Ti}_{25}\text{O}_{60}$
	MgTi_2O_5
Mg-Nb-O	$\text{Mg}_3\text{Nb}_6\text{O}_{11}$
	$\text{Mg}_4\text{Nb}_2\text{O}_9$
	MgNb_2O_6
Mg-Ga-O	MgGa_2O_4

Mg-Al-O	MgAl ₂ O ₄
Mg-Ge-O	Mg ₁₄ Ge ₅ O ₂₄
	Mg ₂ GeO ₄
	MgGeO ₃

S2. Input parameters for DFT calculations

For compounds not available in the Materials Project database¹, we perform density functional theory (DFT)^{2, 3} calculations as implemented in the Vienna Ab initio Simulation Package (VASP).^{4,5} We use the Perdew-Burke-Ernzerhof (PBE) parametrization of the generalized gradient approximation (GGA) to describe the electronic exchange and correlation.⁶ The wave functions of the valence electrons are expanded with a plane-wave basis using a well-converged energy cutoff of 520 eV, whereas the core electrons are treated with the projector augmented wave (PAW) scheme.⁷ The Brillouin-zone integration is carried out on a Monkhorst-Pack⁸ k -point mesh with reciprocal density of 64 k -points per Å⁻¹. The total energy is converged within 5*10⁻⁵ eV/atom.

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